

MOSFET – Power, Single N-Channel

100 V, 20 mΩ, 41 A

NVD6824NL

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- High Current Capability
- Avalanche Energy Specified
- AEC-Q101 Qualified
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	100	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JC}$ (Note 1)	I_D	$T_C = 25^\circ\text{C}$	41
		$T_C = 100^\circ\text{C}$	
Power Dissipation $R_{\theta JC}$ (Note 1)	P_D	$T_C = 25^\circ\text{C}$	90
		$T_C = 100^\circ\text{C}$	
Continuous Drain Current $R_{\theta JA}$ (Notes 1 & 2)	I_D	$T_A = 25^\circ\text{C}$	8.5
		$T_A = 100^\circ\text{C}$	
Power Dissipation $R_{\theta JA}$ (Notes 1 & 2)	P_D	$T_A = 25^\circ\text{C}$	3.9
		$T_A = 100^\circ\text{C}$	
Pulsed Drain Current	I_{DM}	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	238
Current Limited by Package (Note 3)	$I_{Dmaxpkg}$	$T_A = 25^\circ\text{C}$	60
Operating Junction and Storage Temperature	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$
Source Current (Body Diode)	I_S	41	A
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}, V_{GS} = 10 \text{ V}, I_{L(pk)} = 40 \text{ A}, L = 0.1 \text{ mH}, R_G = 25 \Omega$)	E_{AS}	80	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

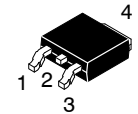
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

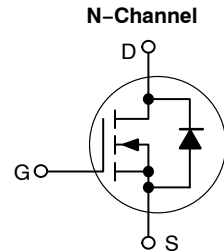
Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Drain)	$R_{\theta JC}$	1.7	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	39	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Continuous DC current rating. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

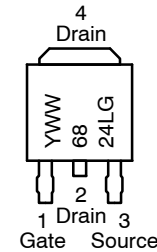
$V_{(BR)DSS}$	$R_{DS(on)}$	I_D
100 V	20 mΩ @ 10 V	41 A
	23 mΩ @ 4.5 V	



DPAK
CASE 369C
STYLE 2



MARKING DIAGRAMS & PIN ASSIGNMENT



Y = Year
 WW = Work Week
 6824L = Device Code
 G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping†
NVD6824NLT4G	DPAK (Pb-Free)	2500/Tape & Reel
NVD6824NLT4G-VF01 NVD6824NLT4G-UM	DPAK (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NVD6824NL

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	100			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			92		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 100 V	T _J = 25°C		1.0	μA
			T _J = 125°C		100	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	1.5		2.5	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			-6.5		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		16.5	20	mΩ
		V _{GS} = 4.5 V, I _D = 20 A		18.5	23	
Forward Transconductance	g _{FS}	V _{DS} = 15 V, I _D = 20 A		18		S

CHARGES, CAPACITANCES AND GATE RESISTANCES

Input Capacitance	C _{iss}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 25 V		3468		pF
Output Capacitance	C _{oss}			187		
Reverse Transfer Capacitance	C _{rss}			133		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 80 V, I _D = 20 A		34		nC
		V _{GS} = 10 V, V _{DS} = 80 V, I _D = 20 A		66		
Threshold Gate Charge	Q _{G(TH)}	V _{GS} = 10 V, V _{DS} = 80 V, I _D = 20 A		3.5		
Gate-to-Source Charge	Q _{GS}			9.0		
Gate-to-Drain Charge	Q _{GD}			18		

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	t _{d(on)}	V _{GS} = 10 V, V _{DD} = 80 V, I _D = 20 A, R _G = 2.5 Ω		15		ns
Rise Time	t _r			55		
Turn-Off Delay Time	t _{d(off)}			31		
Fall Time	t _f			42		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 20 A	T _J = 25°C		0.84	1.2	V
			T _J = 125°C		0.71		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 20 A		38		ns	
Charge Time	t _a			28			
Discharge Time	t _b			10			
Reverse Recovery Charge	Q _{RR}			59		nC	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
- Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

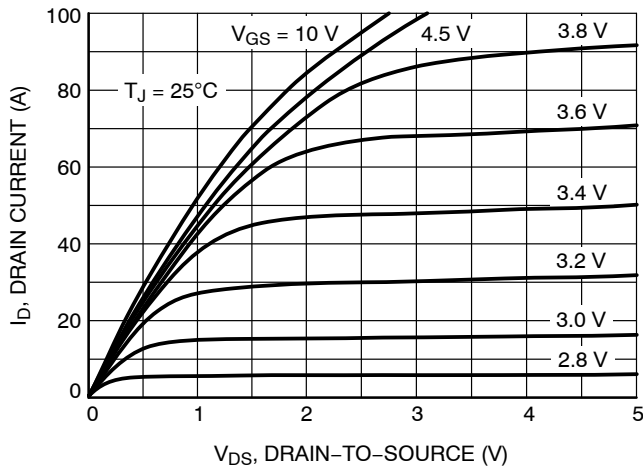


Figure 1. On-Region Characteristics

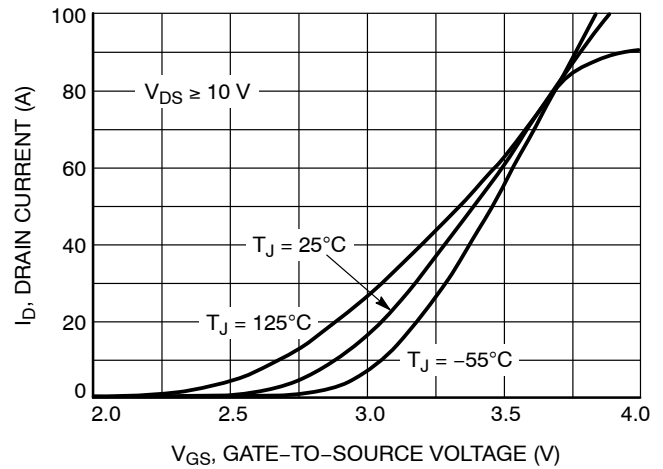


Figure 2. Transfer Characteristics

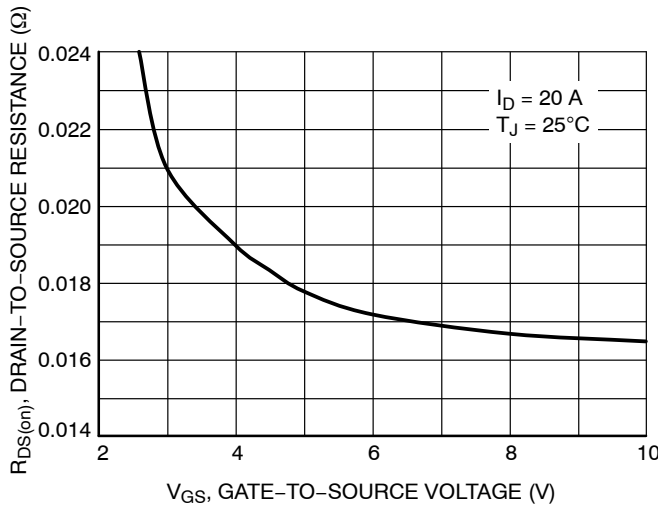


Figure 3. On-Resistance vs. Gate Voltage

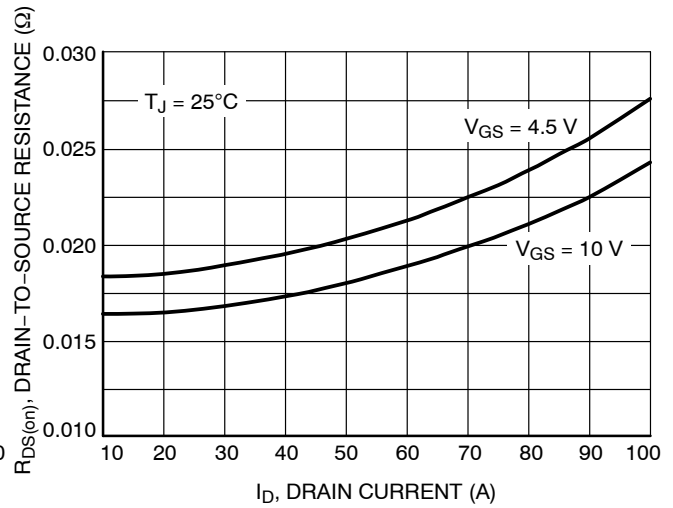


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

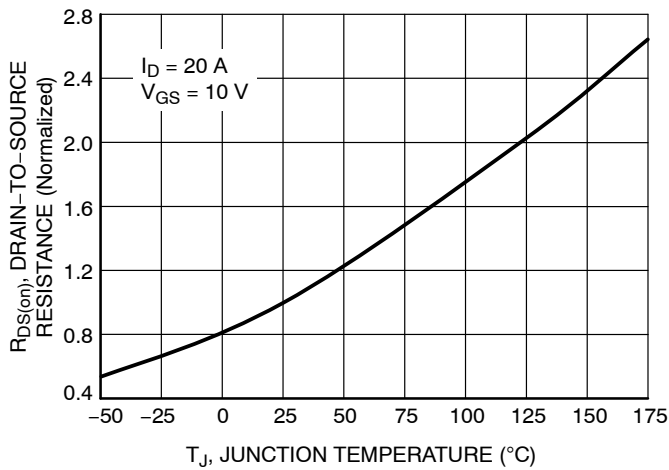


Figure 5. On-Resistance Variation with Temperature

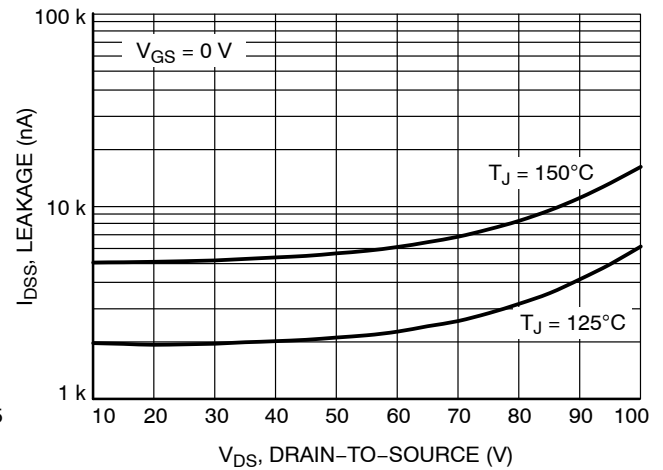


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

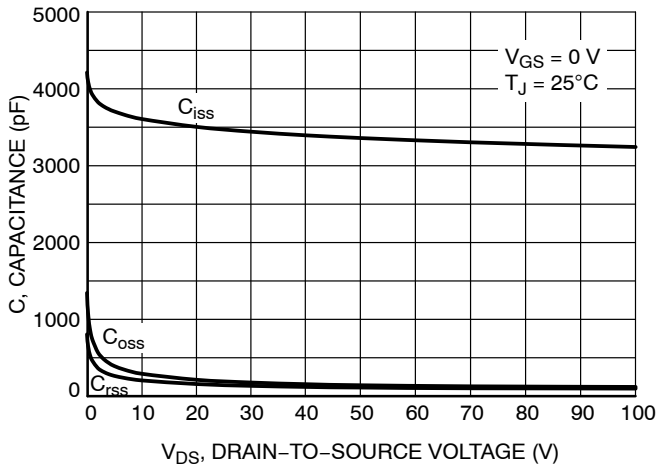


Figure 7. Capacitance Variation

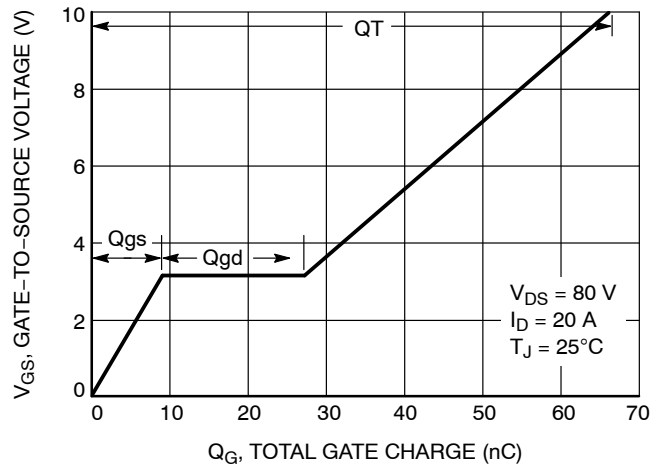


Figure 8. Gate-to-Source Voltage vs. Total Charge

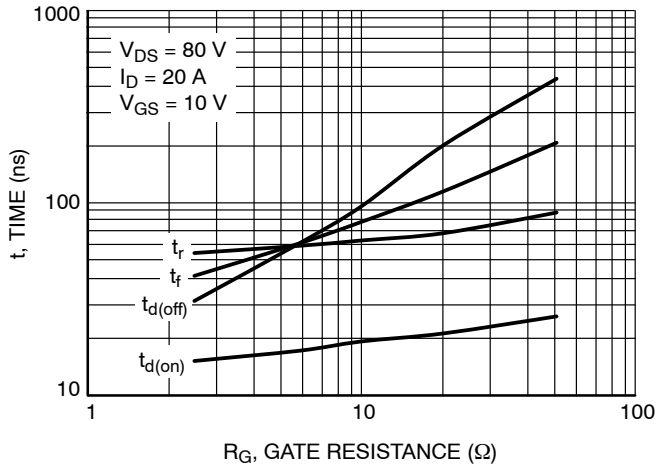


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

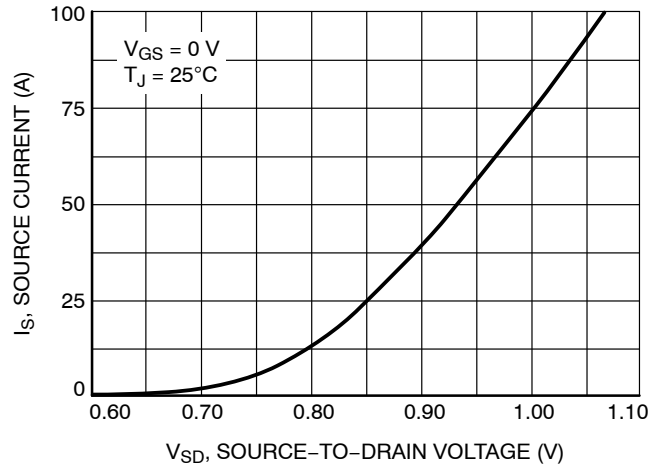


Figure 10. Diode Forward Voltage vs. Current

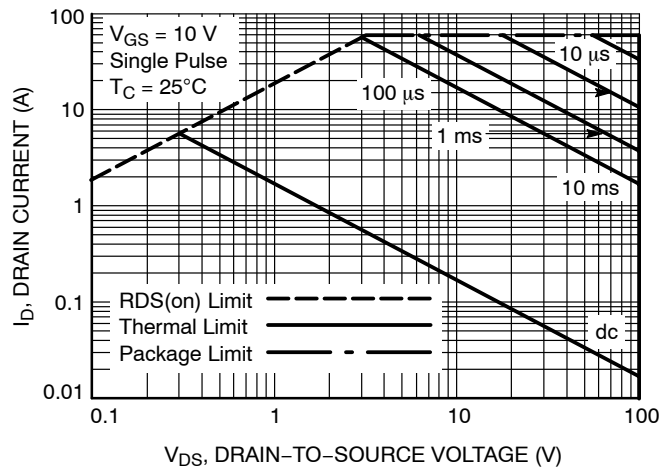


Figure 11. Maximum Rated Forward Biased Safe Operating Area

NVD6824NL

TYPICAL CHARACTERISTICS

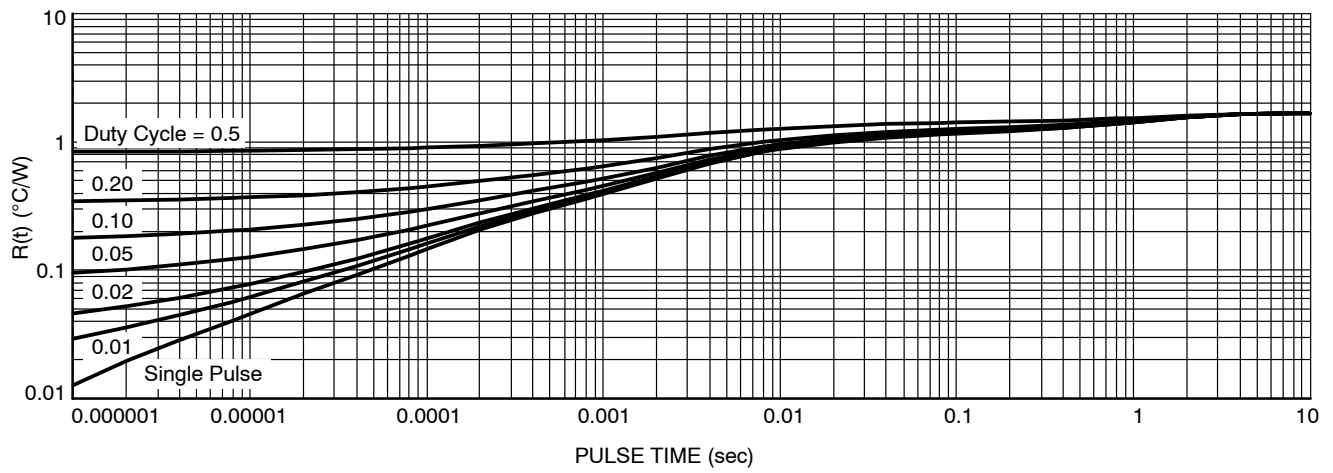
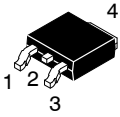


Figure 12. Thermal Response

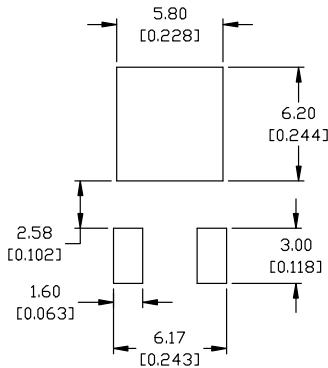
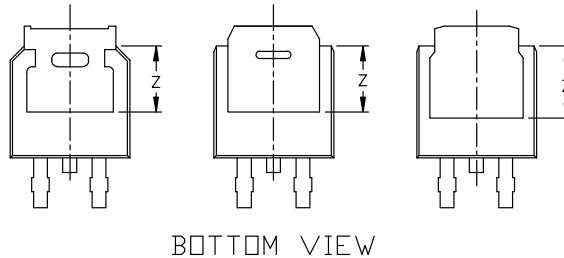
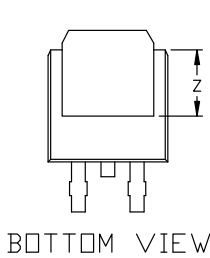
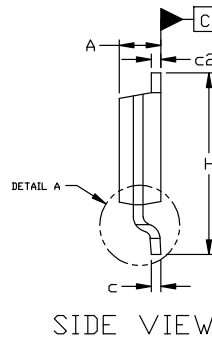
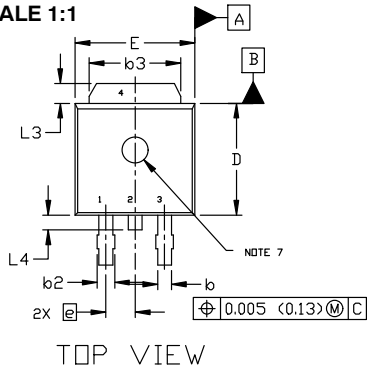
PACKAGE DIMENSIONS

DPAK (SINGLE GAUGE)
CASE 369C
ISSUE G

DATE 31 MAY 2023



SCALE 1:1



RECOMMENDED MOUNTING FOOTPRINT*

*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 8:
PIN 1. N/C
2. CATHODE
3. ANODE
4. CATHODE

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. RESISTOR ADJUST
4. CATHODE

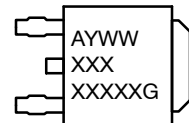
STYLE 10:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

NOTES:

1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	----	0.040	---	1.01
Z	0.155	----	3.93	---

GENERIC MARKING DIAGRAM*



XXXXXX = Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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